

# 2SC4617

## NPN Silicon General Purpose Amplifier Transistor

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SC-75/SOT-416 package which is designed for low power surface mount applications, where board space is at a premium.

### Features

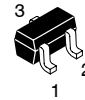
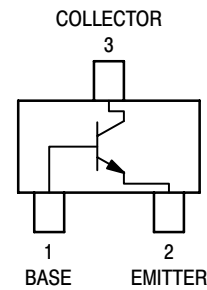
- Pb-Free Package is Available\*
- Reduces Board Space
- High  $h_{FE}$ , 210–460 (typical)
- Low  $V_{CE(sat)}$ , < 0.5 V
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel



**ON Semiconductor®**

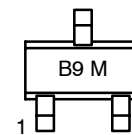
<http://onsemi.com>

### NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



SC-75  
CASE 463  
STYLE 1

### MARKING DIAGRAM



B9 = Specific Device Code  
M = Date Code

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 135 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2SC4617

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>(BR)CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>(BR)CEO</sub>	50	Vdc
Emitter-Base Voltage	V <sub>(BR)EBO</sub>	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	100	mA <sub>dc</sub>

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	125	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 ~ +150	°C

5. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage (I <sub>C</sub> = 50 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 50 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	-	-	Vdc
Collector-Base Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	0.5	μA
Emitter-Base Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>B</sub> = 0)	I <sub>EBO</sub>	-	-	0.5	μA
Collector-Emitter Saturation Voltage (Note 6) (I <sub>C</sub> = 60 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	-	-	0.4	Vdc
DC Current Gain (Note 6) (V <sub>CE</sub> = 6.0 Vdc, I <sub>C</sub> = 1.0 mA <sub>dc</sub> )	h <sub>FE</sub>	120	-	560	-
Transition Frequency (V <sub>CE</sub> = 12 Vdc, I <sub>C</sub> = 2.0 mA <sub>dc</sub> , f = 30 MHz)	f <sub>T</sub>	-	180	-	MHz
Output Capacitance (V <sub>CB</sub> = 12 Vdc, I <sub>C</sub> = 0 A <sub>dc</sub> , f = 1 MHz)	C <sub>OB</sub>	-	2.0	-	pF

6. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
2SC4617	SC-75	3,000 / Tape & Reel
2SC4617G	SC-75 (Pb-Free)	3,000 / Tape & Reel
2SC4617T1	SC-75	3,000 / Tape & Reel
2SC4617T1G	SC-75 (Pb-Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL ELECTRICAL CHARACTERISTICS

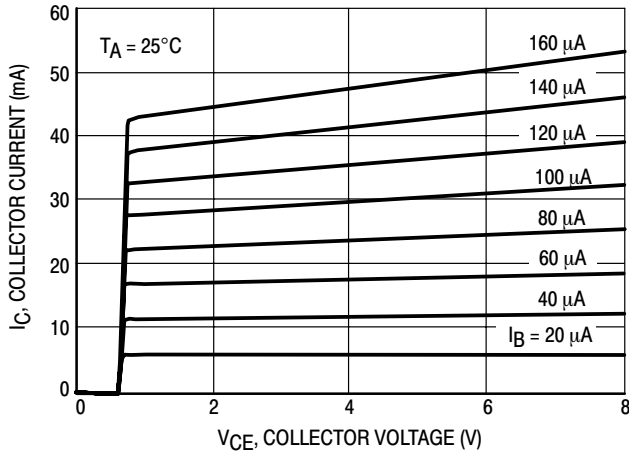


Figure 1.  $I_C - V_{CE}$

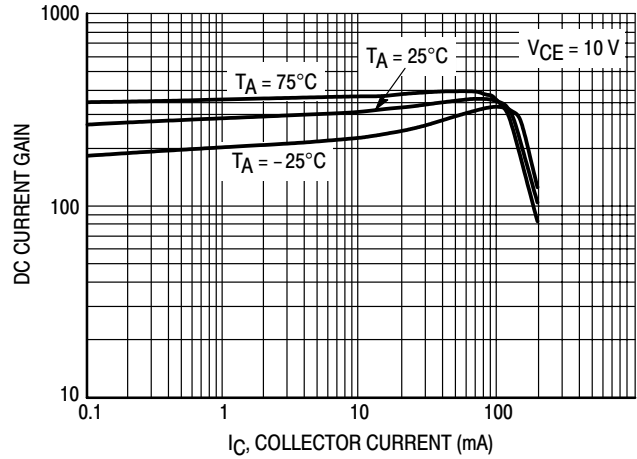


Figure 2. DC Current Gain

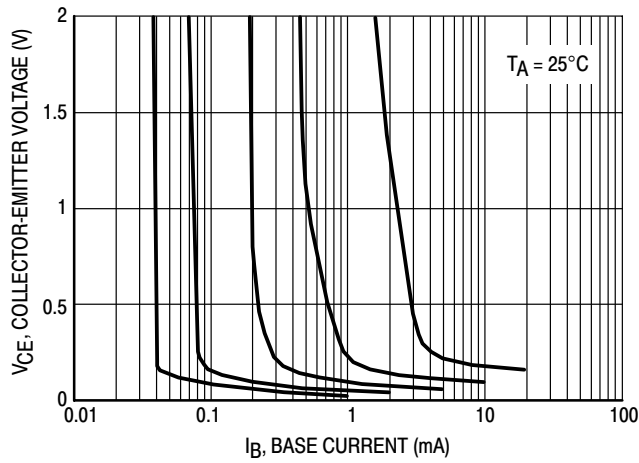


Figure 3. Collector Saturation Region

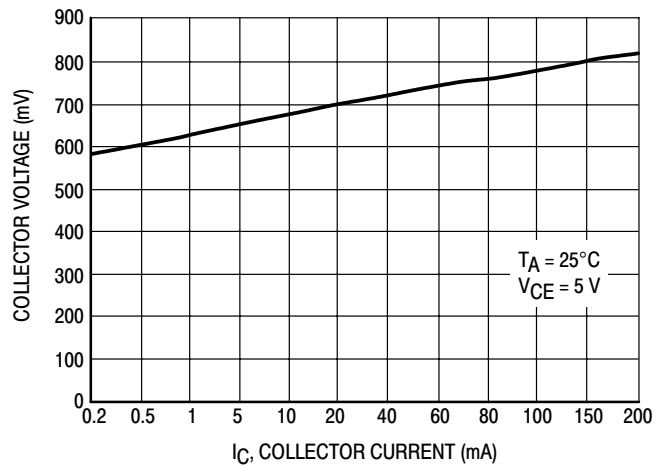


Figure 4. On Voltage

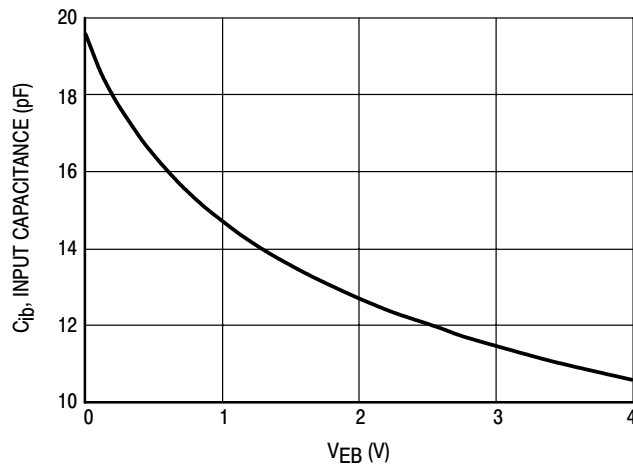


Figure 5. Capacitance

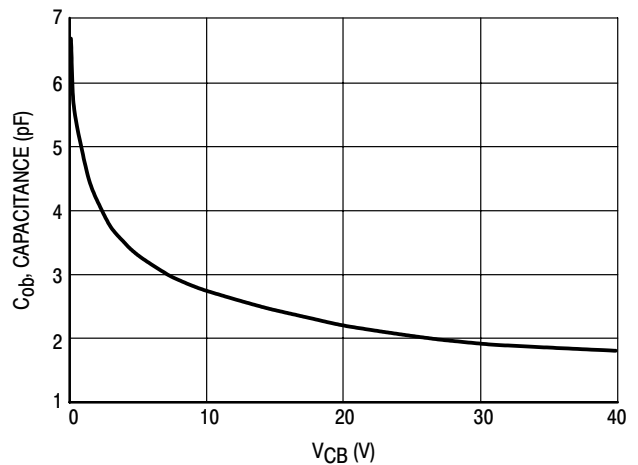


Figure 6. Capacitance